# Heavy-element dependence of thermoelectric properties in Fe<sub>2</sub>VAl thin films Toyota Tech. Inst.<sup>1</sup>, NIMS.<sup>2</sup>

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**[Introduction]** Heusler-type Fe<sub>2</sub>VAI-based compounds consisting of non-toxic and abundant materials have been widely investigated as one of the most promising thermoelectric materials. Although its power factor reaches 5.5 mWm<sup>-1</sup>K<sup>-2</sup> which is even larger than that of Bi<sub>2</sub>Te<sub>3</sub>-based thermoelectric materials, the figure of merit is still much less than unity due to the high lattice thermal conductivity of more than 20 W m<sup>-1</sup>K<sup>-1</sup>. As for that, we tried to reduce the thermal conductivity through two approaches, doping control using heavy elements and fabricating thin films which successfully decreased to 7.2 and 12.6 Wm<sup>-1</sup>K<sup>-1</sup>, respectively.<sup>1,2</sup> In the present study, we intended to enhance the thermoelectric properties by doping Ta in in the Fe<sub>2</sub>VAI-based thin films, that is, by combining the both approaches.

**[Experimental procedure]** The thin film samples consisting of Ta-doped Fe<sub>2</sub>VAl were prepared on the (100) surface of MgO single crystal substrates by means of the radio frequency magnetron sputtering technique. The out-of-plane XRD measurement along cross-plane direction and phi scan around MgO 202 and Fe<sub>2</sub>VAl 404 reflections. The chemical composition of thin film was analyzed using electron-probe micro-analyzer. The electrical resistivity and thermal conductivity were precisely measured using conventional 4-probe method and pico-seconds time-domain thermo-reflectance method, respectively.

**[Results and discussion]** The figure definitely shows that Ta-doping leads to the remarkable reduction of thermal conductivity. Thus, we focused on the effect of Ta doping into Fe<sub>2</sub>VAl-based thin films. In the presentation, the thermoelectric properties as a function of Ta content in Fe<sub>2</sub>VAl thin films will be mainly discussed.

#### References

- 1. Y. Terazawa et al., J. Electron. Mater., **41**, 1348 (2011).
- 2. S. Hiroi et al., Mater. Trans. 57, 1628 (2016).

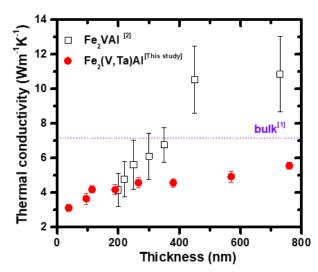


Figure. Thickness dependence of thermal conductivity for Fe<sub>2</sub>VAl and Fe<sub>2</sub>(V,Ta)Al.